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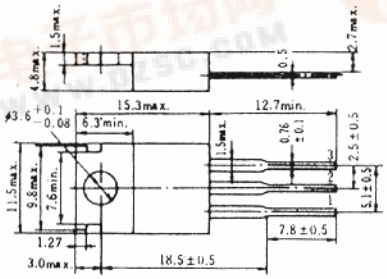
2SB856

SILICON PNP TRIPLE DIFFUSED

LOW FREQUENCY POWER AMPLIFIER



1. Base
2. Collector (Flange)
3. Emitter

(Dimensions in mm)

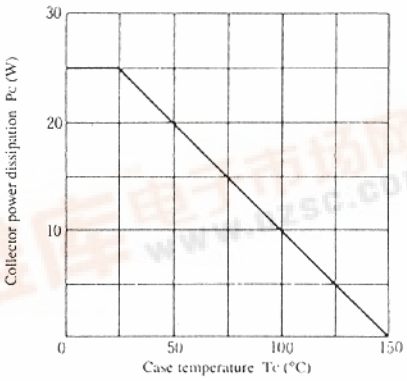
(JEDEC TO-220AB)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB856	Unit
Collector to base voltage	V_{CBO}	−50	V
Collector to emitter voltage	V_{CEO}	−50	V
Emitter to base voltage	V_{EBO}	−4	V
Collector current	I_C	−3	A
Collector power dissipation	P_C*	25	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−45 to +150	°C

* Value at Tc = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = −5mA, I_E = 0	−50	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = −50mA, R_{BE} = ∞	−50	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = −5mA, I_C = 0	−4	—	—	V
Collector cutoff current	I_{CBO}	V_{CB} = −20V, I_E = 0	—	—	−100	μA
DC current transfer ratio	h_{FE1}*	V_{CE} = −4V, I_C = −1A**	35	—	200	
	h_{FE2}	V_{CE} = −4V, I_C = −0.1A**	35	—	—	
Base to emitter voltage	V_{BE}	V_{CE} = −4V, I_C = −1A**	—	—	−1.5	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = −2A, I_B = −0.2A**	—	—	−1.2	V
Gain bandwidth product	f_T	V_{CE} = −4V, I_C = −0.5A**	—	35	—	MHz

* The 2SB856 is grouped by h_{FE1} as follows.

** Pulse Test

A	B	C
35 to 70	60 to 120	100 to 200

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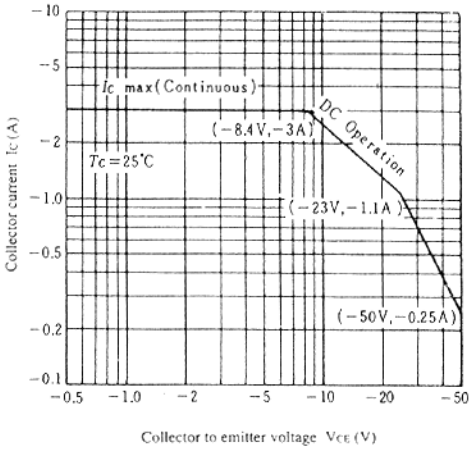
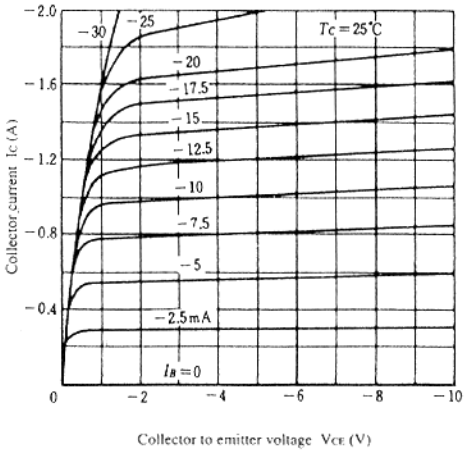
HITACHI

2SB856

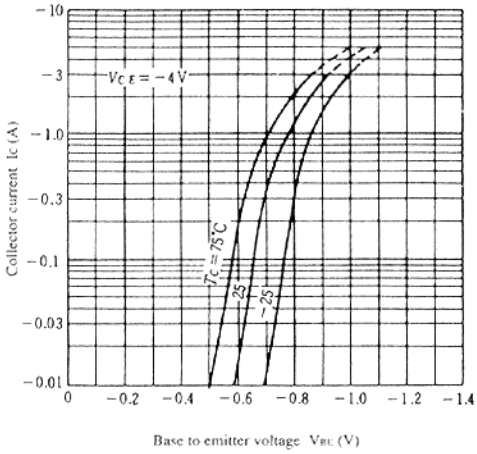
AREA OF SAFE OPERATION



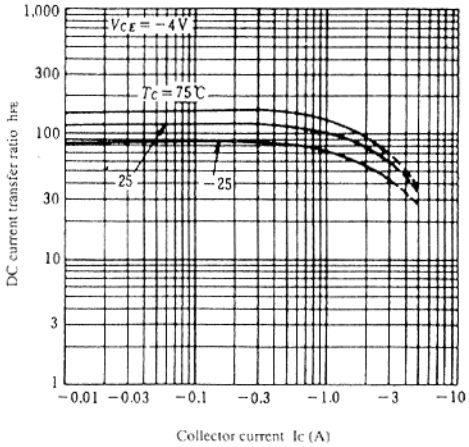
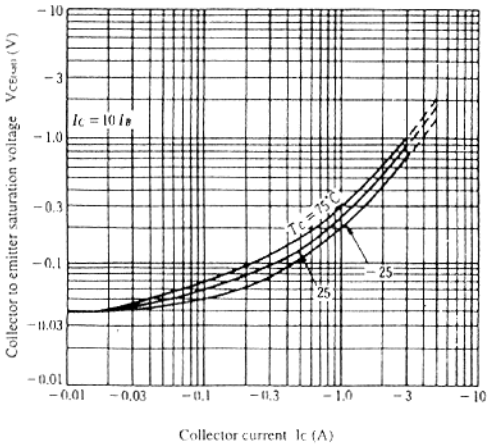
TYPICAL OUTPUT CHARACTERISTICS



TYPICAL TRANSFER CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT